MOSFETs Silicon P-Channel MOS (U-MOSVI)

TPCF8107

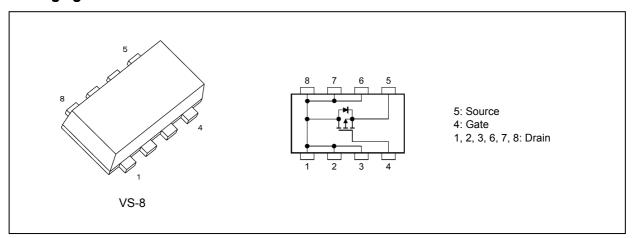
1. Applications

- · Lithium-Ion Secondary Batteries
- · Power Management Switches
- · Notebook PCs

2. Features

- (1) Small footprint due to a small and thin package
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 22 \text{ m}\Omega$ (typ.) ($V_{GS} = -10 \text{ V}$)
- (3) Low leakage current: $I_{DSS} = -10 \mu A \text{ (max) (V}_{DS} = -30 \text{ V)}$
- (4) Enhancement mode: V_{th} = -0.8 to -2.0 V (V_{DS} = -10 V, I_D = -0.1 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteris	Symbol	Rating	Unit		
Drain-source voltage			V_{DSS}	-30	V
Gate-source voltage			V _{GSS}	-25/+20	
Drain current (DC)		(Note 1)	I _D	-6	Α
Drain current (pulsed)		(Note 1)	I _{DP}	-24	
Power dissipation	(t = 5 s)	(Note 2)	P _D	2.5	W
Power dissipation	(t = 5 s)	(Note 3)	P_{D}	0.7	W
Single-pulse avalanche energy		(Note 4)	E _{AS}	23.4	mJ
Avalanche current			I _{AR}	-6	Α
Channel temperature	•		T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



5. Thermal Characteristics

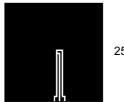
Characteristics			Symbol	Max	Unit
Channel-to-ambient thermal resistance	(t = 5 s)	(Note 2)	R _{th(ch-a)}	50.0	°C/W
Channel-to-ambient thermal resistance	(t = 5 s)	(Note 3)	R _{th(ch-a)}	178.5	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

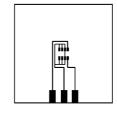
Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: V_{DD} = -24 V, T_{ch} = 25°C (initial), L = 0.5 mH, R_G = 25 Ω , I_{AR} = -6 A



 $\begin{aligned} & \text{FR-4} \\ 25.4 \times 25.4 \times 0.8 \\ & \text{(Unit: mm)} \end{aligned}$



FR-4 $25.4 \times 25.4 \times 0.8$ (Unit: mm)

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics (T_a = 25°C unless otherwise specified)

6.1. Static Characteristics

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μА
Drain cut-off current	I _{DSS}	V _{DS} = -30 V, V _{GS} = 0 V	_	_	-10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = -10 mA, V _{GS} = 0 V	-30	_	_	V
Drain-source breakdown voltage (Note 5)	V _{(BR)DSX}	I _D = -10 mA, V _{GS} = 10 V	-21	_		
Gate threshold voltage	V_{th}	$V_{DS} = -10 \text{ V}, I_{D} = -0.1 \text{ mA}$	-0.8	_	-2.0	
Drain-source on-resistance	R _{DS(ON)}	$V_{GS} = -4.5 \text{ V}, I_D = -3 \text{ A}$	_	29	38	mΩ
		$V_{GS} = -10 \text{ V}, I_D = -3 \text{ A}$	_	22	28	

Note 5: If a forward bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	_	970	_	pF
Reverse transfer capacitance	C _{rss}		_	170	_	
Output capacitance	C _{oss}		_	200	_	
Switching time (rise time)	t _r	See Figure 6.2.1.	_	7.5	_	ns
Switching time (turn-on time)	t _{on}	1	_	14	_	
Switching time (fall time)	t _f	1	_	33	_	
Switching time (turn-off time)	t _{off}]	_	116	_	

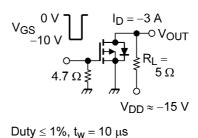


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx -24 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -6 \text{ A}$	_	22	_	nC
Gate-source charge 1	Q _{gs1}		_	2.4	_	
Gate-drain charge	Q _{gd}		_	5.4	_	

6.4. Source-Drain Characteristics

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Pulsed reverse drain current (Not	e 6) I _{DRP}	_	_		-24	Α
Diode forward voltage	V _{DSF}	I _{DR} = -6 A, V _{GS} = 0 V	_	_	1.2	V

Note 6: Ensure that the channel temperature does not exceed 150°C.



7. Marking

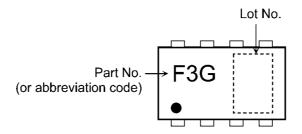


Fig. 7.1 Marking

8. Characteristics Curves (Note)

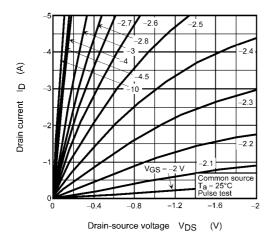


Fig. 8.1 $I_D - V_{DS}$

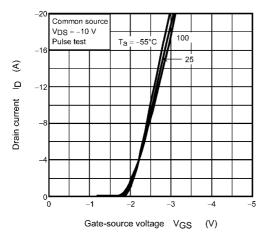


Fig. 8.3 I_D - V_{GS}

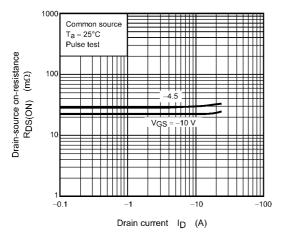


Fig. 8.5 R_{DS(ON)} - I_D

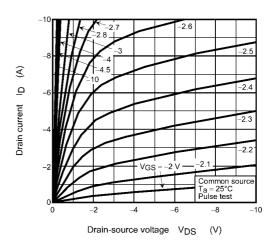


Fig. 8.2 $I_D - V_{DS}$

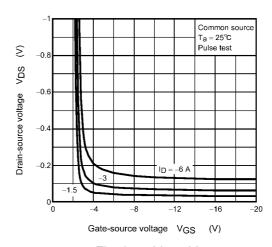


Fig. 8.4 V_{DS} - V_{GS}

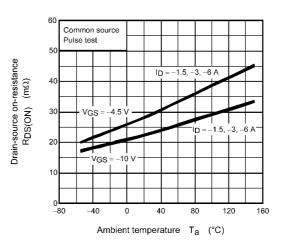


Fig. 8.6 R_{DS(ON)} - T_a

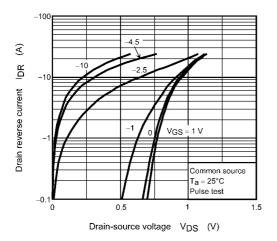


Fig. 8.7 IDR - VDS

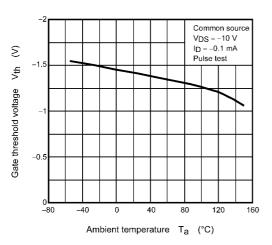


Fig. 8.9 V_{th} - T_a

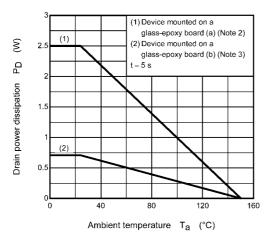


Fig. 8.11 P_D - T_a (Guaranteed Maximum)

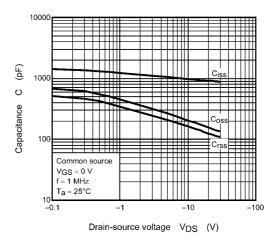


Fig. 8.8 Capacitance - V_{DS}

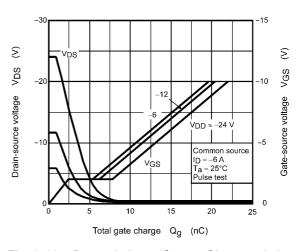


Fig. 8.10 Dynamic Input/Output Characteristics

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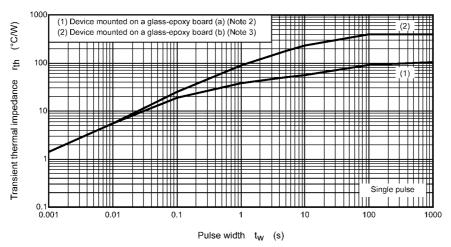


Fig. 8.12 r_{th} - t_w (Guaranteed Maximum)

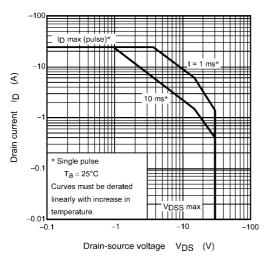


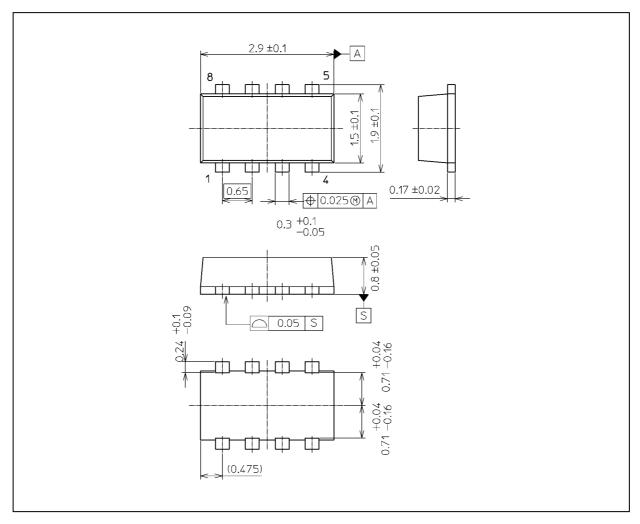
Fig. 8.13 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.011 g (typ.)

Package Name(s)	
TOSHIBA: 2-3U1S	
Nickname: VS-8	

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